



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	21mΩ @ V _{GS} = 10V	10A

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

Features and Benefits

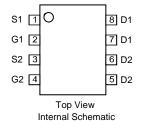
- Low On-Resistance
- Low Input Capacitance
- Low Input/Output Leakage
- Low Gate Resistance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

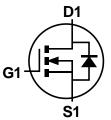
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)

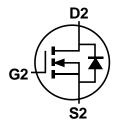


Top View





N-Channel MOSFET



N-Channel MOSFET

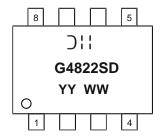
Ordering Information (Note 5)

Part Number	Case	Packaging
DMG4822SSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- $5. \ For packaging \ details, go \ to \ our \ website \ at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

Marking Information



⊃¦¦ = Manufacturer's Marking G4822SD = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 17 = 2017) WW = Week (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	10 6.6	А
Pulsed Drain Current (Note 7)			I _{DM}	60	Α
Avalanche Current (Notes 8 & 9)			I _{AR}	1.68	Α
Repetitive Avalanche Energy, L = 0.3mH (Notes 8 & 9)			E _{AR}	12.8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	1.42	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	88.4	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Tyn	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)	Symbol	IVIIII	Тур	IVIAX	Onit	rest Condition	
, ,	T 5)/	20			V	N/ 01/ 1 050::A	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_		-	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 30V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	13.4	21	mΩ	$V_{GS} = 10V, I_D = 8.5A$	
Static Dialif-Source Off-Resistance	R _{DS(ON)}	-	19.5	32.5	11122	$V_{GS} = 4.5V, I_D = 6A$	
Forward Transfer Admittance	Y _{fs}		20	_	mS	$V_{DS} = 5V, I_{D} = 8.5A$	
Diode Forward Voltage	V _{SD}		0.4	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 11)						<u> </u>	
Input Capacitance	C _{iss}	_	478.9	_	pF	101/1/	
Output Capacitance	Coss	_	96.7	_	pF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	61.4	_	pF		
Gate Resistance	Rg	_	1.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	5	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_{g}	_	10.5	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$ $I_{D} = 8.5A$	
Gate-Source Charge	Q_{gs}	_	1.8	_	nC		
Gate-Drain Charge	Q _{gd}		1.6	_	nC		
Turn-On Delay Time	t _{D(ON)}		2.9	_	ns	$V_{DS} = 15V, V_{GS} = 10V,$ $R_L = 1.8\Omega, R_G = 3\Omega$	
Turn-On Rise Time	t _R	_	7.9	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	14.6	_	ns		
Turn-Off Fall Time	t _F	_	3.1	_	ns		

Notes:

^{6.} Device mounted on FR-4 PCB, with minimum recommended pad layout.
7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
8. Repetitive rating, pulse width limited by junction temperature.

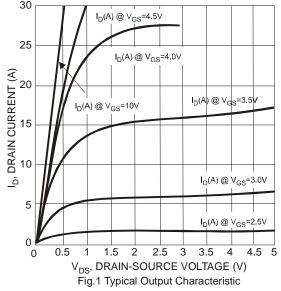
^{9.} I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

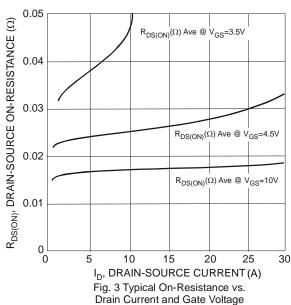
^{10.} Short duration pulse test used to minimize self-heating effect.

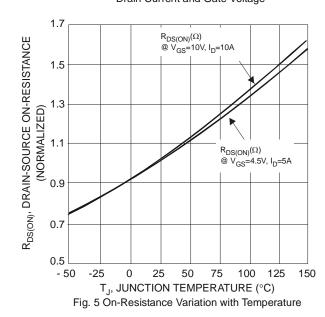
^{11.} Guaranteed by design. Not subject to product testing.

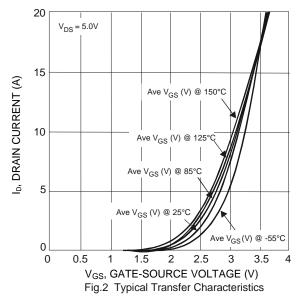


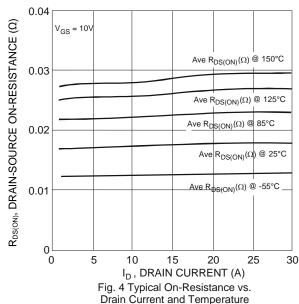


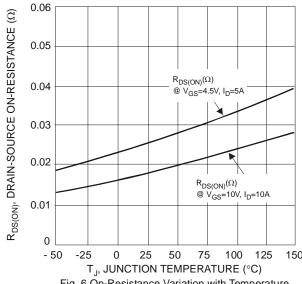














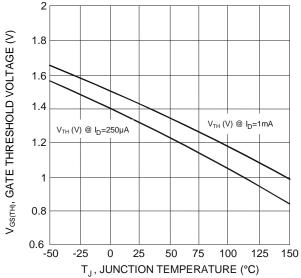


Fig. 7 Gate Threshold Variation vs. Junction Temperature

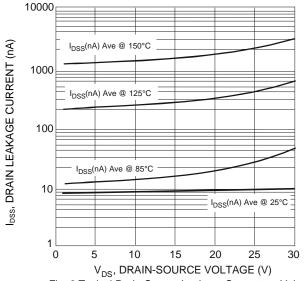
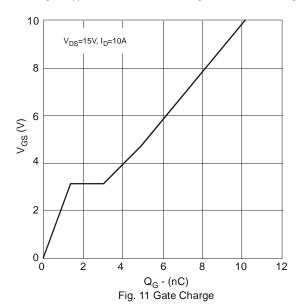
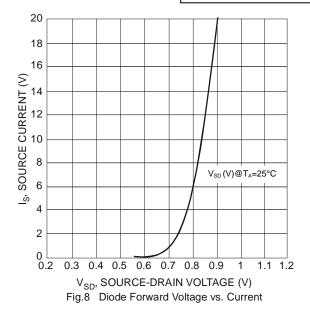
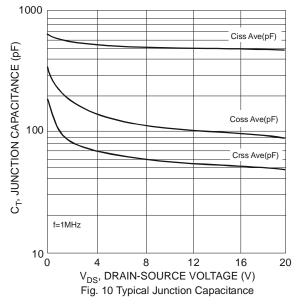


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage









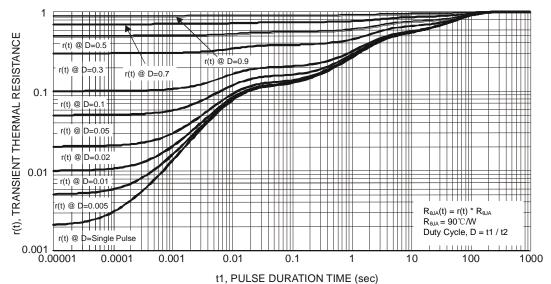


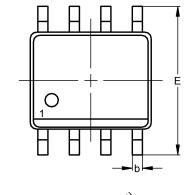
Fig. 12 Transient Thermal Resistance

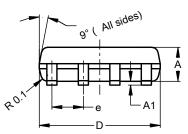


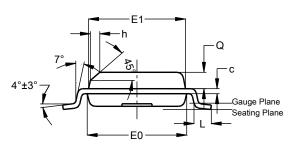
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





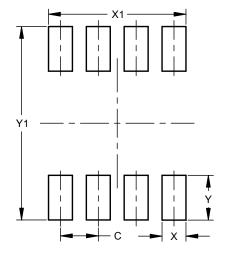


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е	1		1.27		
h	1		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)		
С	1.27		
Х	0.802		
X1	4.612		
Y	1.505		
V1	6.50		



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